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**FIG.1: Power dissipation vs. on-state current**  
(per thyristor or diode)  
 $P_{T(AV)}/P_{F(AV)}(W)$

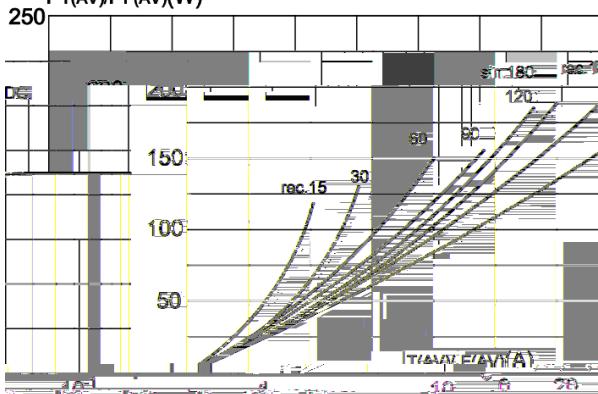


**FIG.2: Maximum transient thermal impedance**  
junction to case(per thyristor or diode)  
 $R_{th(j-c)}(^{\circ}C/W)$

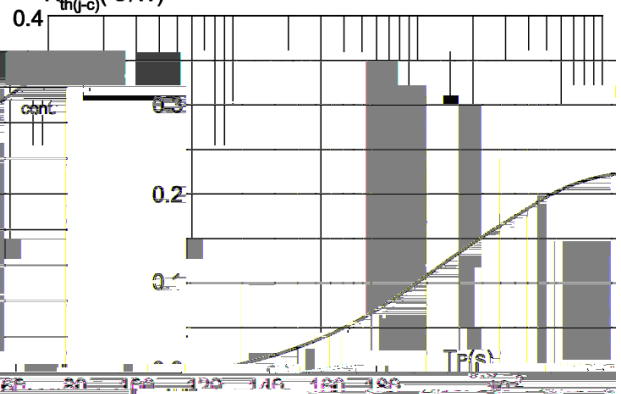


**FIG.3: Forward characteristics**

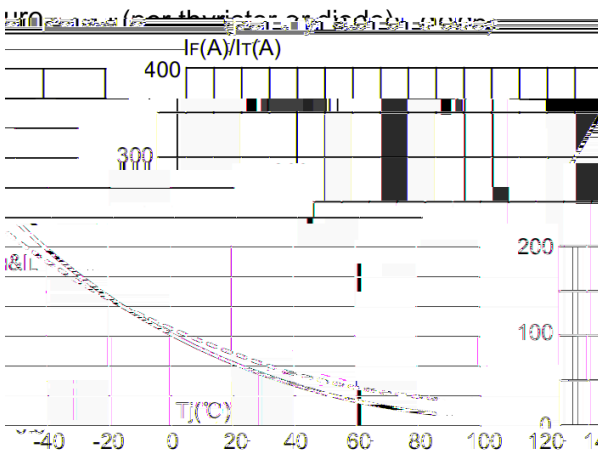


**FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature**

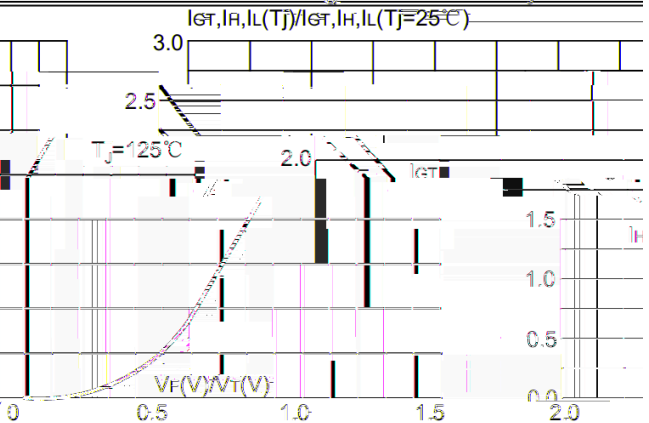


**FIG.5: Gate trigger characteristics**

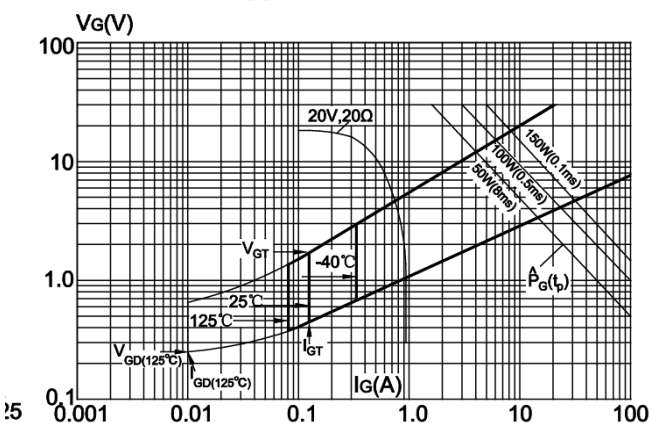


**FIG.6: Forward current vs. case temperature**  
 $I_{F(AV)}(A)$  (per thyristor or diode)

